

AMENDMENTS TO THE SPECIFICATION

On page 8, lines 9-21 should be replaced with

FIGURE 1a shows a cross section of a substrate 100 with topography features 110, which has been processed with a layer 120 to be patterned using lithography. The next step is to apply a photosensitive material, typically a photoresist polymer to form a coating ~~130~~ of photoresist 130. This material is not always perfectly conformal, as illustrated in FIGURE 1b.

FIGURE 1c shows exposure of the photosensitive material using selective exposure to photons or charged particles. Images are formed of several features on a photomask (not shown) by focussing the image on the surface of the layer 120 without topography. For this illustration, the images are of identical dimensions. Exposure of these identical features is shown schematically as identical exposure beams 150 with a waist at the point of smallest focus. The exposure is typically for a set duration of time, with a certain exposure fluence to deliver a specified dose of photons or charged particles to the photosensitive material.